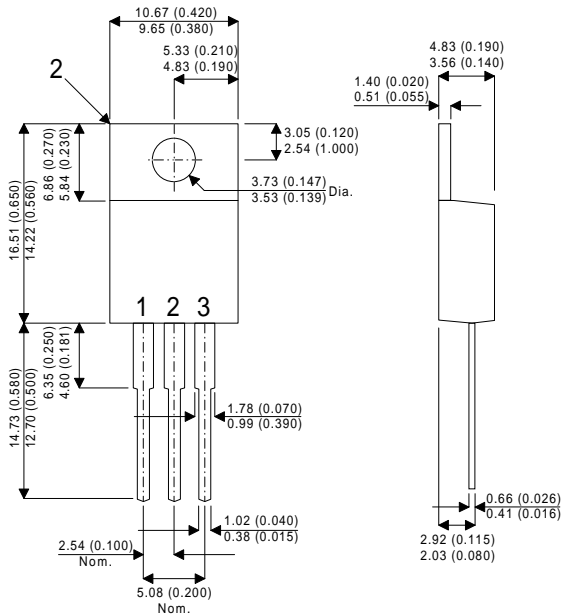


4TH GENERATION MOSFET

TO220-AC Package Outline.
Dimensions in mm (inches)



Pin 1 — Gate Pin 2 — Drain Pin 3 — Source

**N-CHANNEL
ENHANCEMENT MODE
HIGH VOLTAGE
POWER MOSFETS**

V_{DS} 1000V
 $I_{D(cont)}$ 3.6A
 $R_{DS(on)}$ 4.00Ω

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{DS}	Drain – Source Voltage	1000	V
I_D	Continuous Drain Current	3.6	A
I_{DM}	Pulsed Drain Current ¹	14.4	A
V_{GS}	Gate – Source Voltage	±30	V
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	125	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature : 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	1000			V
$I_{D(ON)}$	On State Drain Current ²	$V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max $V_{GS} = 10V$	3.6			A
$R_{DS(ON)}$	Drain – Source On State Resistance ²	$V_{GS} = 10V, I_D = 0.5 I_D [Cont.]$			4.00	Ω
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0V$)	$V_{DS} = V_{DSS}$			250	μA
		$V_{DS} = 0.8V_{DSS}, T_C = 125^{\circ}C$			1000	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1.0mA$	2		4	V

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width < 380μS , Duty Cycle < 2%

DYNAMIC CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		805	950	pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		115	160	
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		37	60	
Q_g	Total Gate Charge ³	$V_{GS} = 10V$		35	55	nC
Q_{gs}	Gate – Source Charge	$V_{DD} = 0.5 V_{DSS}$		4.3	6.5	
Q_{gd}	Gate – Drain (“Miller”) Charge	$I_D = I_D [Cont.]$		18	27	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$		10	20	ns
t_r	Rise Time	$V_{DD} = 0.5 V_{DSS}$		9	18	
$t_{d(off)}$	Turn-off Delay Time	$I_D = I_D [Cont.]$		32	48	
t_f	Fall Time	$R_G = 1.8\Omega$		23	46	

SOURCE – DRAIN DIODE RATINGS AND CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current (Body Diode)				3.6	A
I_{SM}	Pulsed Source Current ¹ (Body Diode)				14.4	
V_{SD}	Diode Forward Voltage ²	$V_{GS} = 0V, I_S = -I_D [Cont.]$			1.3	V
t_{rr}	Reverse Recovery Time	$I_S = -I_D [Cont.]$ $di_S / dt = 100A/\mu s$	150	290	580	ns
Q_{rr}	Reverse Recovery Charge		0.8	1.65	3.3	μC

SAFE OPERATING AREA CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
SOA1	Safe Operating Area	$V_{DS} = 0.4V_{DSS}, t = 1 Sec.$ $I_{DS} = P_D / 0.4V_{DSS}$	125			W
SOA2	Safe Operating Area	$V_{DS} = P_D / I_D [Cont.]$ $I_{DS} = I_D [Cont.], t = 1 Sec.$	125			W
I_{LM}	Inductive Current Clamped		14.4			A

THERMAL CHARACTERISTICS

	Characteristic	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction to Case			1.0	$^{\circ}C/W$
$R_{\theta JA}$	Junction to Ambient			80	

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width < 380 μs , Duty Cycle < 2%

3) See MIL–STD–750 Method 3471



CAUTION — Electrostatic Sensitive Devices. Anti-Static Procedures Must Be Followed.